

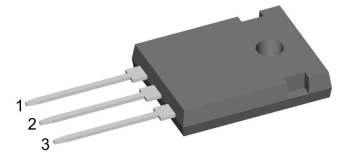
High Efficiency Thyristor

$V_{RRM} = 1200\text{ V}$
 $I_{TAV} = 40\text{ A}$
 $V_T = 1,26\text{ V}$

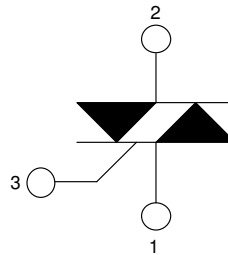
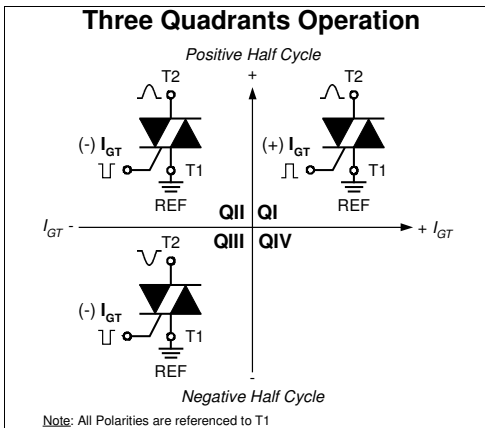
Three Quadrants operation: QI - QIII
 1~ Triac

Part number

CLA80MT1200NHB



Backside: Terminal 2



Features / Advantages:

- Triac for line frequency
- Three Quadrants Operation
 - QI - QIII
- Planar passivated chip
- Long-term stability of blocking currents and voltages

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

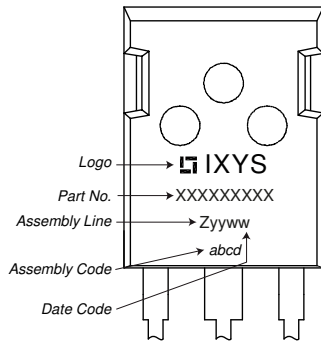
- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
I_{RD}	reverse current, drain current	$V_{R/D} = 1200 V$	$T_{VJ} = 25^{\circ}C$		10	μA	
		$V_{R/D} = 1200 V$	$T_{VJ} = 125^{\circ}C$		2	mA	
V_T	forward voltage drop	$I_T = 40 A$	$T_{VJ} = 25^{\circ}C$		1,30	V	
		$I_T = 80 A$			1,59	V	
		$I_T = 40 A$	$T_{VJ} = 125^{\circ}C$		1,26	V	
		$I_T = 80 A$			1,64	V	
I_{TAV}	average forward current	$T_C = 120^{\circ}C$	$T_{VJ} = 150^{\circ}C$		40	A	
I_{RMS}	RMS forward current per phase	180° sine			88	A	
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0,88	V	
r_T	slope resistance				10	m Ω	
R_{thJC}	thermal resistance junction to case				0,4	K/W	
R_{thCH}	thermal resistance case to heatsink			0,25		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		310	W	
I_{TSM}	max. forward surge current	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		520	A	
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		560	A	
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 150^{\circ}C$		440	A	
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		475	A	
I^2t	value for fusing	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		1,35	kA ² s	
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		1,31	kA ² s	
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 150^{\circ}C$		970	A ² s	
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		940	A ² s	
C_J	junction capacitance	$V_R = 400 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		25	pF	
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 150^{\circ}C$		10	W	
		$t_p = 300 \mu s$			5	W	
P_{GAV}	average gate power dissipation				0,5	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}C; f = 50 Hz$ repetitive, $I_T = 120 A$			150	A/ μs	
		$t_p = 200 \mu s; di_G/dt = 0,3 A/\mu s;$ $I_G = 0,3 A; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 40 A$			500	A/ μs	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		500	V/ μs	
		$R_{GK} = \infty$; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1,7	V	
			$T_{VJ} = -40^{\circ}C$		1,9	V	
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		± 70	mA	
			$T_{VJ} = -40^{\circ}C$		± 90	mA	
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		0,2	V	
I_{GD}	gate non-trigger current				± 1	mA	
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		100	mA	
		$I_G = 0,3 A; di_G/dt = 0,3 A/\mu s$					
I_H	holding current	$V_D = 6 V R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		70	mA	
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs	
		$I_G = 0,3 A; di_G/dt = 0,3 A/\mu s$					
t_q	turn-off time	$V_R = 100 V; I_T = 40 A; V = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s dv/dt = 20 V/\mu s t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		150	μs	

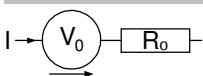
Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			70	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				6		g
M_D	mounting torque		0,8		1,2	Nm
F_C	mounting force with clip		20		120	N

Product Marking

Part description

- C = Thyristor (SCR)
- L = High Efficiency Thyristor
- A = (up to 1200V)
- 80 = Current Rating [A]
- MT = 1~ Triac
- 1200 = Reverse Voltage [V]
- N = Three Quadrants operation: QI - QIII
- HB = TO-247AD (3)

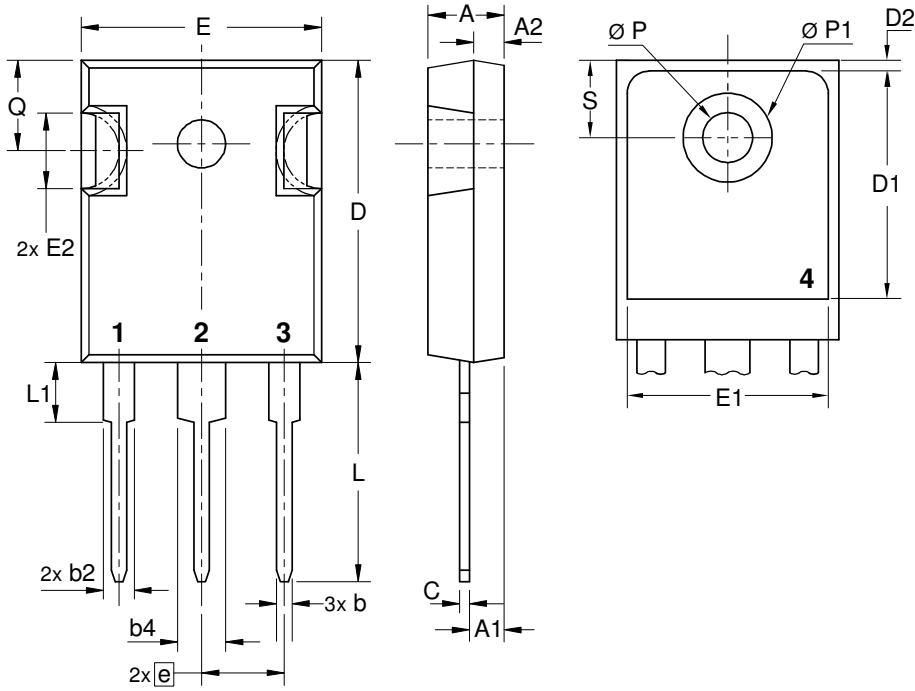
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLA80MT1200NHB	CLA80MT1200NHB	Tube	30	517024

Similar Part	Package	Voltage class
CLA80MT1200NHR	ISO247 (3)	1200

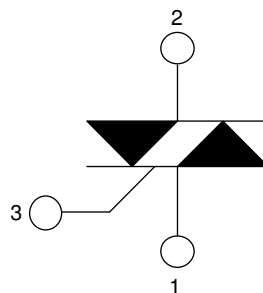
Equivalent Circuits for Simulation
** on die level*
 $T_{VJ} = 150\text{ °C}$

Thyristor

$V_{0\ max}$	threshold voltage	0,88	V
$R_{0\ max}$	slope resistance *	7,5	mΩ

Outlines TO-247



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215 BSC		5.46 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212		5.38	
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



Thyristor

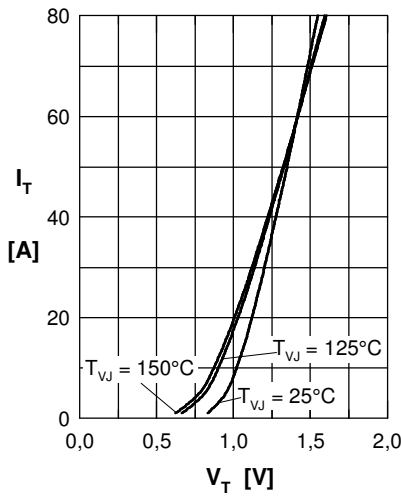


Fig. 1 Forward characteristics

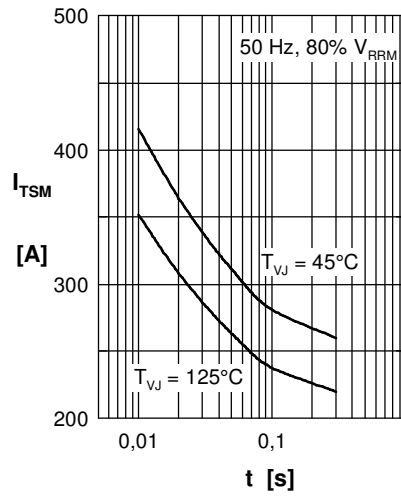


Fig. 2 Surge overload current
 I_{TSM} : crest value, t : duration

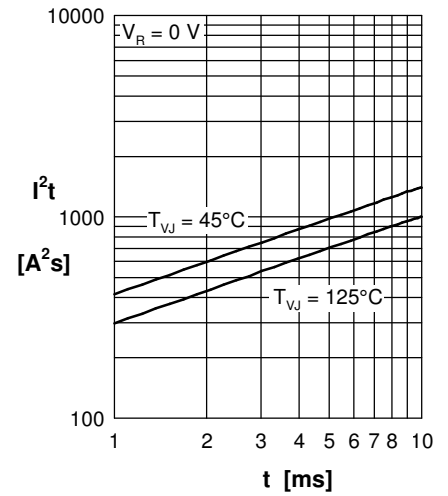


Fig. 3 I^2t versus time (1-10 s)

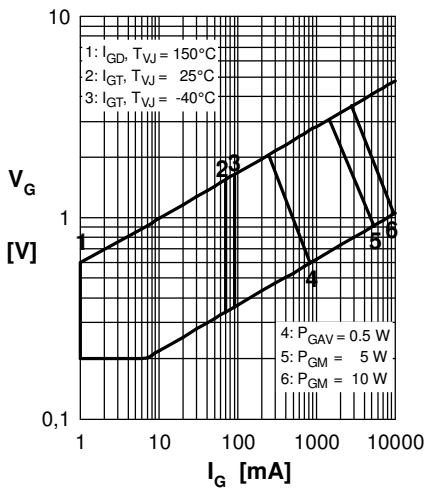


Fig. 4 Gate voltage & gate current

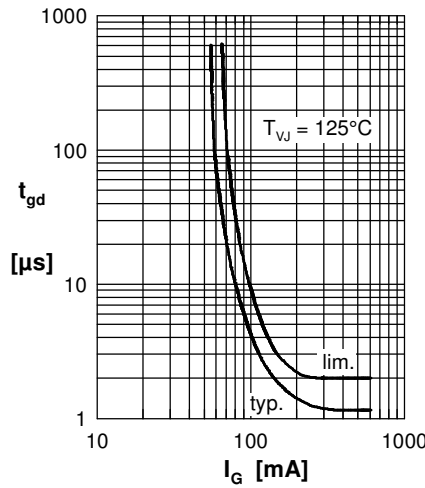


Fig. 5 Gate controlled delay time t_{gd}

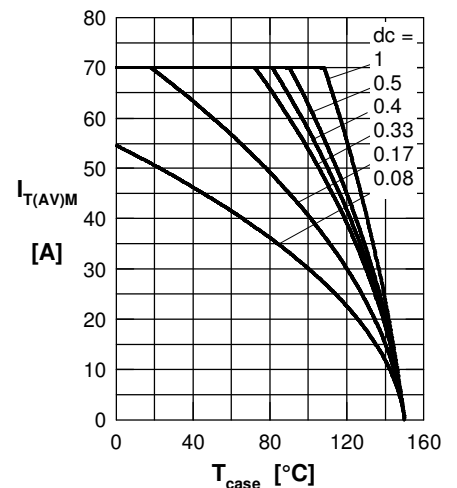


Fig. 6 Max. forward current at case temperature

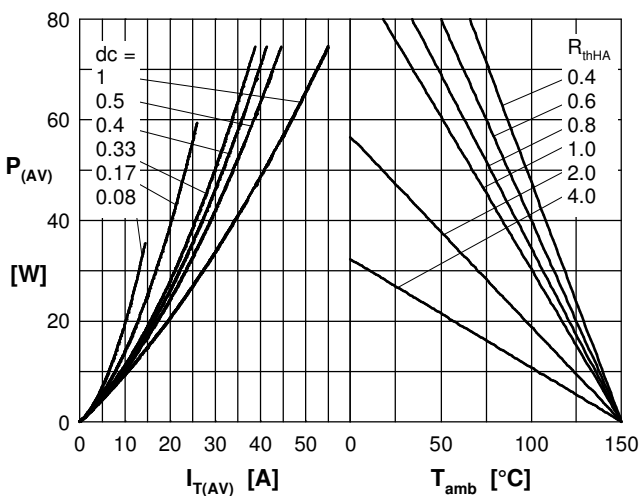


Fig. 7a Power dissipation versus direct output current
Fig. 7b and ambient temperature

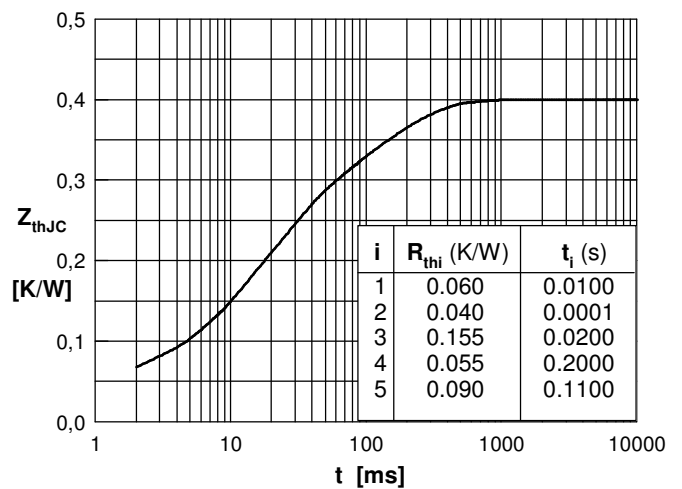


Fig. 7 Transient thermal impedance junction to case